



DCR5890H52

Phase Control Thyristor

DS6159-2 January 2015 (LN32249)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} V	Conditions
DCR5890H52* DCR5890H50 DCR5890H48	5200 5000 4800	$\begin{split} T_{vj} &= \text{-}40^{\circ}\text{C to 125}^{\circ}\text{C}, \\ I_{DRM} &= I_{RRM} = 600\text{mA}, \\ V_{DRM}, V_{RRM}t_p &= 10\text{ms}, \\ V_{DSM}\&V_{RSM} &= \\ V_{DRM}\&V_{RRM} + 100V \\ respectively \end{split}$

Lower voltage grades available. *5000V @ -40°C, 5200V @ 0°C

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR5890H52

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

 $\begin{array}{lll} V_{DRM} & 5200V \\ I_{T(AV)} & 5890A \\ I_{TSM} & 86970A \\ dV/dt^* & 2000V/\mu s \\ dI/dt & 200A/\mu s \\ \end{array}$

* Higher dV/dt selections available

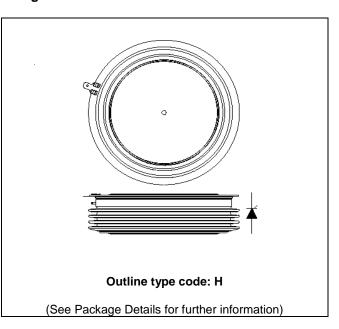


Fig. 1 Package outline



CURRENT RATINGS

$T_{case} = 60$ °C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units	
Double Si	Double Side Cooled				
I _{T(AV)}	Mean on-state current	Half wave resistive load	5890	Α	
I _{T(RMS)}	RMS value	-	9250	А	
I _T	Continuous (direct) on-state current	-	8030	А	

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	86.97	kA
l ² t	I ² t for fusing	$V_R = 0$	37.8	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	-	0.004255	°C/W
		Single side cooled	Anode DC	-	0.008	°C/W
			Cathode DC	-	0.0093	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 135.0kN	Double side	-	0.0009	°C/W
		(with mounting compound)	Single side	-	0.0018	°C/W
T_{vj}	Virtual junction temperature	Blocking V _{DRM} / V _{RRM}		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
F _m	Clamping force			120	155	kN





DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	600	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C, ga	ate open	-	2000	V/µs
dl/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)}	Repetitive 50Hz	-	200	A/µs
		Gate source 30V, 10Ω,	Non-repetitive	-	500	A/µs
		$t_r < 0.5 \mu s, T_j = 125^{\circ}C$				
$V_{T(TO)}$	Threshold voltage – Low level	500 to 4000A at T _{case} = 125°	С	-	0.845	V
	Threshold voltage – High level	4000 to 8000A at T _{case} = 125°C		-	1.15	V
r _T	On-state slope resistance – Low level	500A to 4000A at T _{case} = 125°C		-	0.155	mΩ
	On-state slope resistance – High level	4000A to 8000A at T _{case} = 125°C		-	0.093	mΩ
t _{gd}	Delay time	V_D = 67% V_{DRM} , gate source 30V, 10Ω		-	3	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$\begin{split} I_T &= 3000 A, \ T_j = 125^{\circ} C, \\ V_R &= 200 V, \ dI/dt = 1 A/\mu s, \\ dV_{DR}/dt &= 20 V/\mu s \ linear \end{split}$			700	μs
Qs	Stored charge	- I_T = 3000A, T_j = 125°C, dI/dt - 1A/ μ s, V_{Rpeak} ~3100V, V_R ~ 2100V		3260	8185	μC
I _{RR}	Reverse recovery current			45	77	A
IL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
I _H	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 500A, I_T = 5A$		-	300	mA



GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V_{GT}	Gate trigger voltage	$V_{DRM} = 5V$, $T_{case} = 25$ °C	1.5	V
V_{GD}	Gate non-trigger voltage	At 50% V _{DRM} , T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25$ °C	350	mA
I _{GD}	Gate non-trigger current	At 50% V _{DRM} , T _{case} = 125°C	10	mA

CURVES

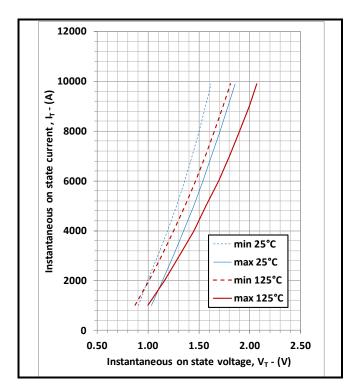


Fig.2 Maximum & minimum on-state characteristics

 V_{TM} EQUATION

 $V_{TM} = A + BIn (I_T) + C.I_T + D.\sqrt{I_T}$

Where A = 2.0256

B = -0.2916

C = -0.00005

D = 0.03214

these values are valid for T_j = 125°C for I_T 500A to 8000A

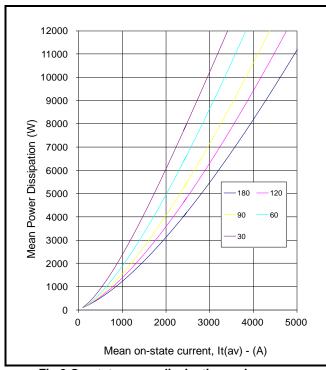


Fig.3 On-state power dissipation - sine wave

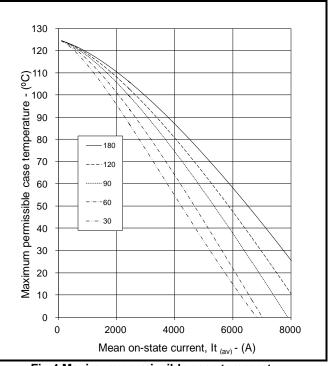


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

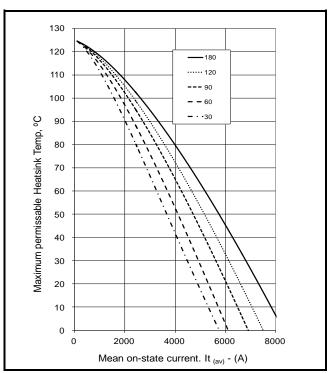


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

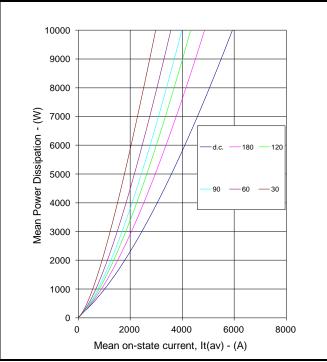


Fig.6 On-state power dissipation - rectangular wave

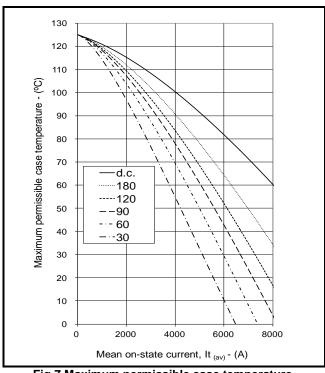


Fig.7 Maximum permissible case temperature, double side cooled – rectangular wave

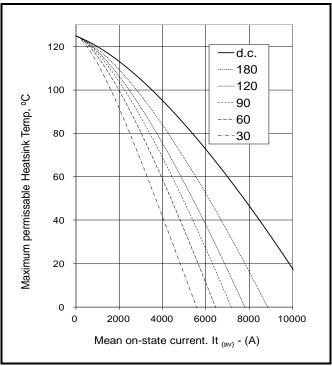


Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave

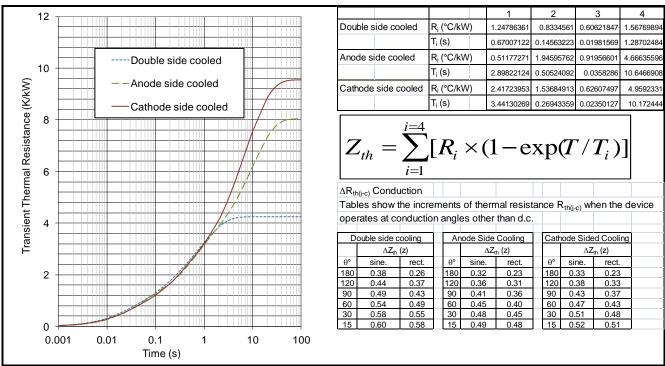
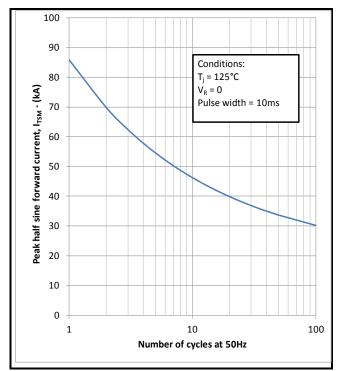


Fig.9 Maximum (limit) transient thermal impedance - junction to case (°C/kW)



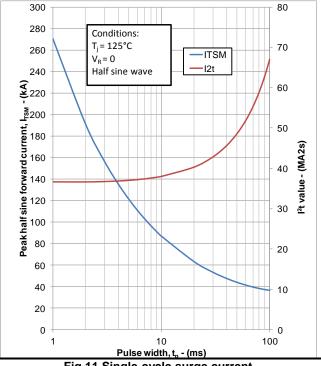
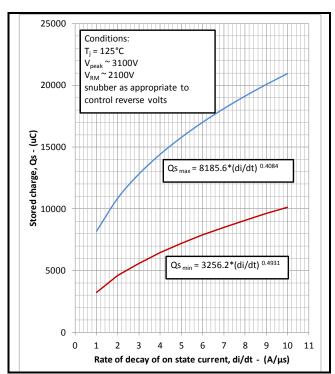


Fig.10 Multi-cycle surge current

Fig.11 Single-cycle surge current





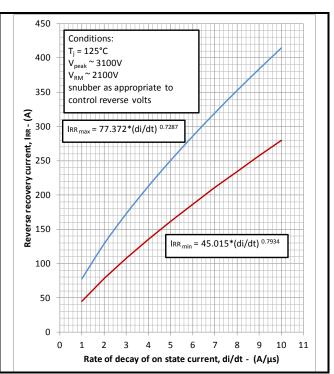


Fig.13 Reverse recovery current

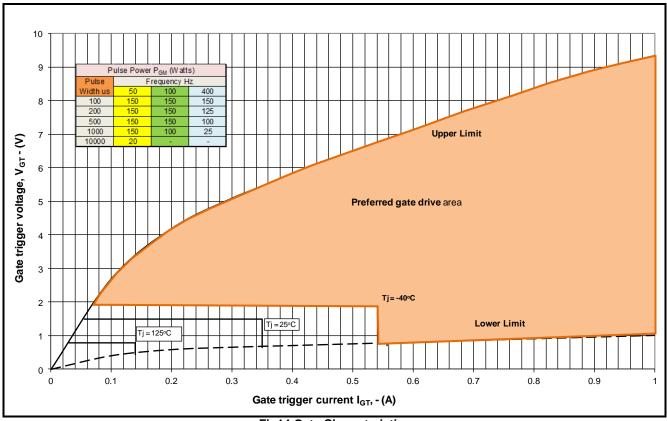


Fig14 Gate Characteristics

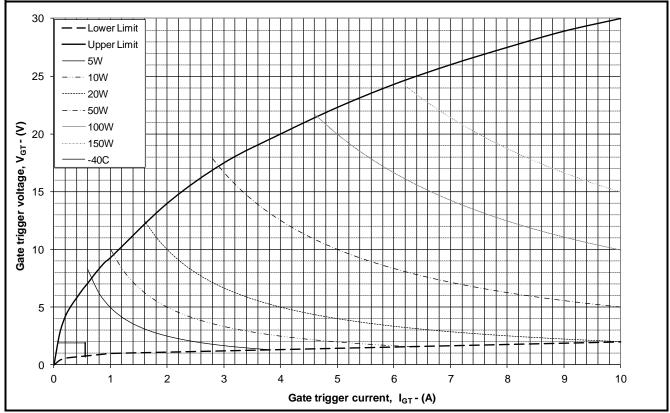


Fig. 15 Gate characteristics





PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

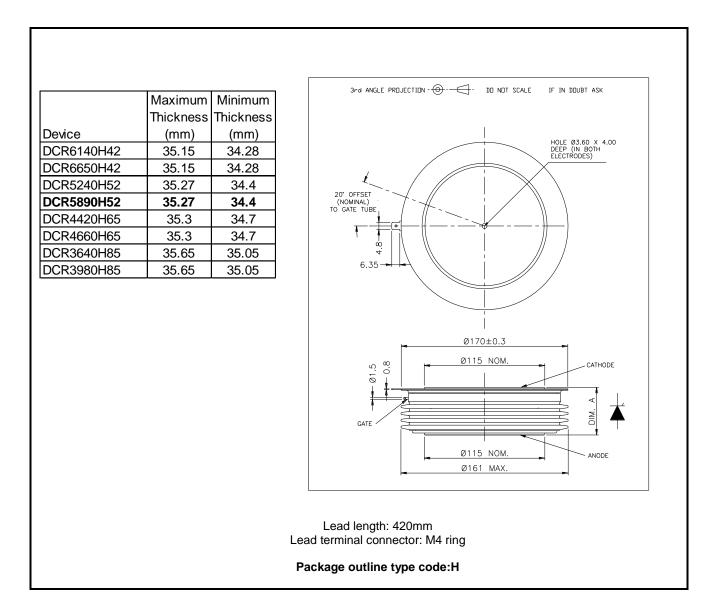


Fig.16 Package outline





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HEADQUARTERS OPERATIONS

DYNEX SEMICONDUCTOR LIMITED
Doddington Road, Lincoln, Lincolnshire, LN6 3LF

United Kingdom.

No Annotation:

Phone: +44 (0) 1522 500500 Fax: +44 (0) 1522 500550 Web: http://www.dynexsemi.com

CUSTOMER SERVICE

Phone: +44 (0) 1522 502753 / 502901 Fax: +44 (0) 1522 500020

e-mail: power_solutions@dynexsemi.com

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